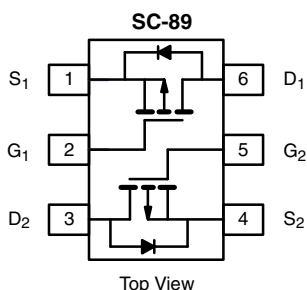


P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (min) (V)	$R_{DS(on)}$ (Ω)	$V_{GS(th)}$ (V)	I_D (mA)
- 60	4 at $V_{GS} = - 10$ V	- 1 to - 3.0	- 500



Marking Code: D

Ordering Information: Si1025X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFETs
- High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 23 pF (typ.)
- Miniature Package
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC


RoHS
COMPLIANT
HALOGEN
FREE

BENEFITS

- Ease in Driving Switches
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven Without Buffer
- Small Board Area

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid State Relays

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 60		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	- 200	- 190	mA
		- 145	- 135	
Pulsed Drain Current ^b	I_{DM}	- 650		
Continuous Source Current (Diode Conduction) ^a	I_S	- 450	- 380	
Maximum Power Dissipation ^a	P_D	280	250	mW
		145	130	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000		V

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

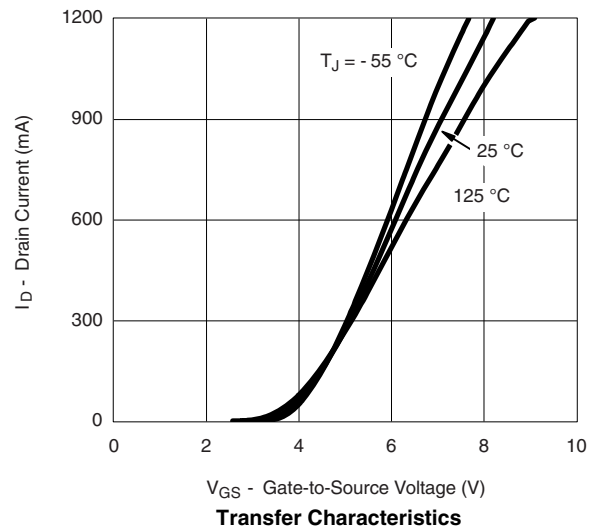
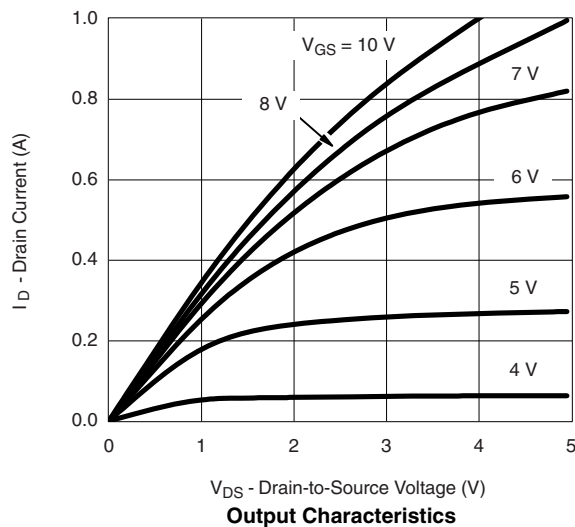
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 10 μA	- 60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 0.25 mA	- 1		- 3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 10 V			± 200	nA
		V _{DS} = 0 V, V _{GS} = ± 5 V			± 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 50 V, V _{GS} = 0 V			- 25	
		V _{DS} = - 50 V, V _{GS} = 0 V, T _J = 85 °C			- 250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 10 V, V _{GS} = - 4.5 V	- 50			mA
		V _{DS} = - 10 V, V _{GS} = - 10 V	- 600			
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 25 mA			8	Ω
		V _{GS} = - 10 V, I _D = - 500 mA			4	
		V _{GS} = - 10 V, I _D = - 500 mA, T _J = 125 °C			6	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 100 mA		100		mS
Diode Forward Voltage ^a	V _{SD}	I _S = - 200 mA, V _{GS} = 0 V			- 1.4	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = - 30 V, V _{GS} = - 15 V, I _D ≅ - 500 mA		1.7		nC
Gate-Source Charge	Q _{gs}			0.26		
Gate-Drain Charge	Q _{gd}			0.46		
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		23		pF
Output Capacitance	C _{oss}			10		
Reverse Transfer Capacitance	C _{rss}			5		
Switching ^{b, c}						
Turn-On Time	t _{ON}	V _{DD} = - 25 V, R _L = 150 Ω, I _D ≅ - 165 mA, V _{GEN} = - 10 V, R _g = 10 Ω		20		ns
Turn-Off Time	t _{OFF}			35		

Notes:

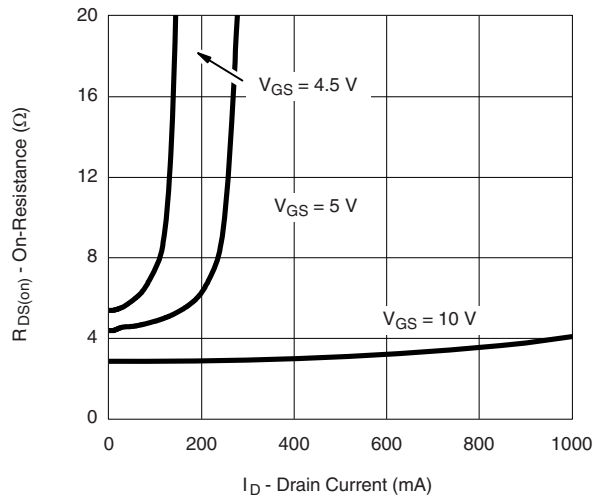
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. For DESIGN AID ONLY, not subject to production testing.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

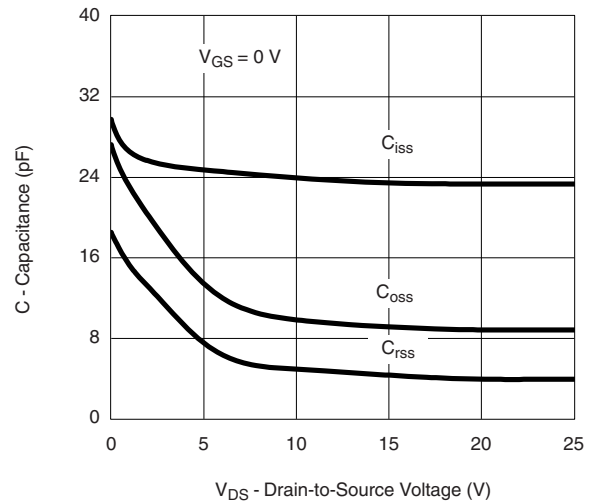
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



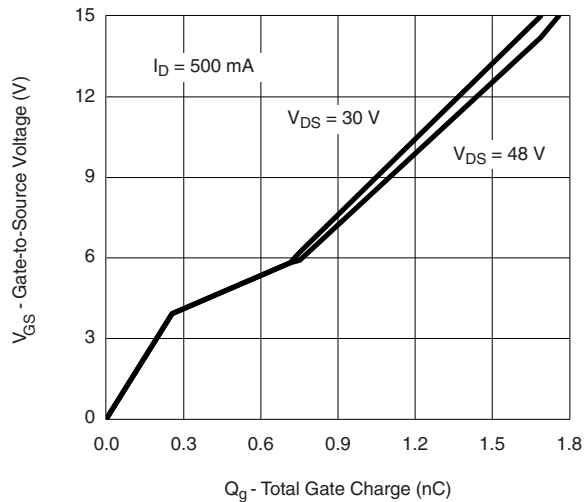
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



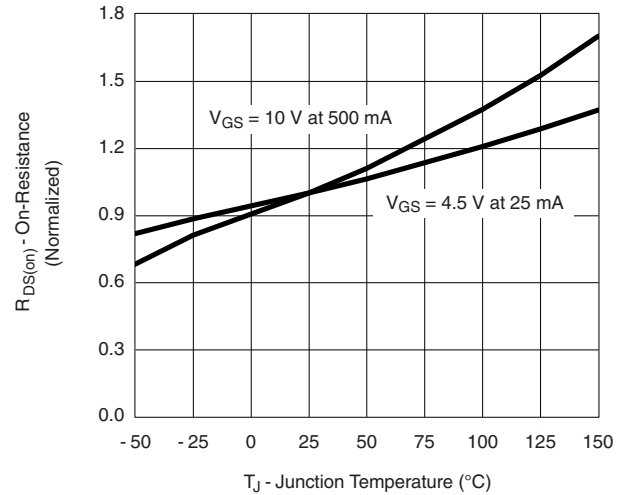
On-Resistance vs. Drain Current



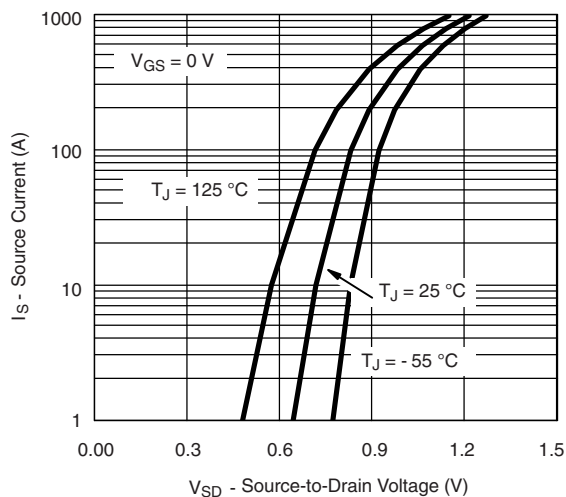
Capacitance



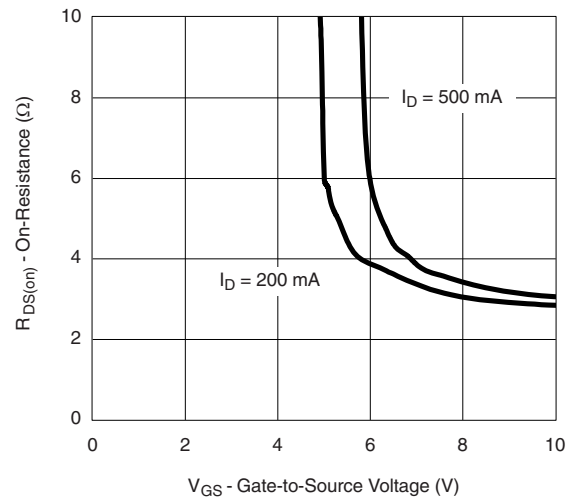
Gate Charge



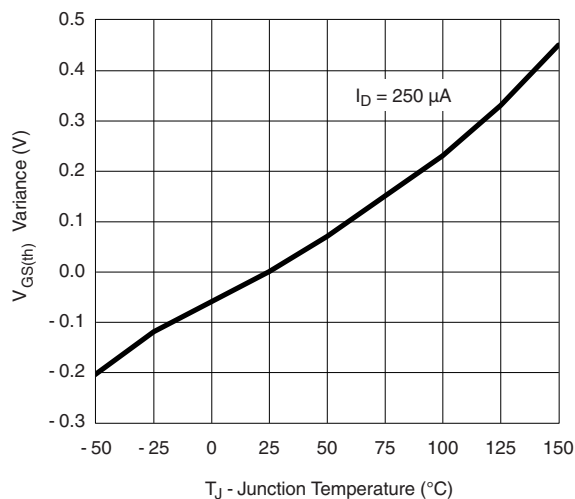
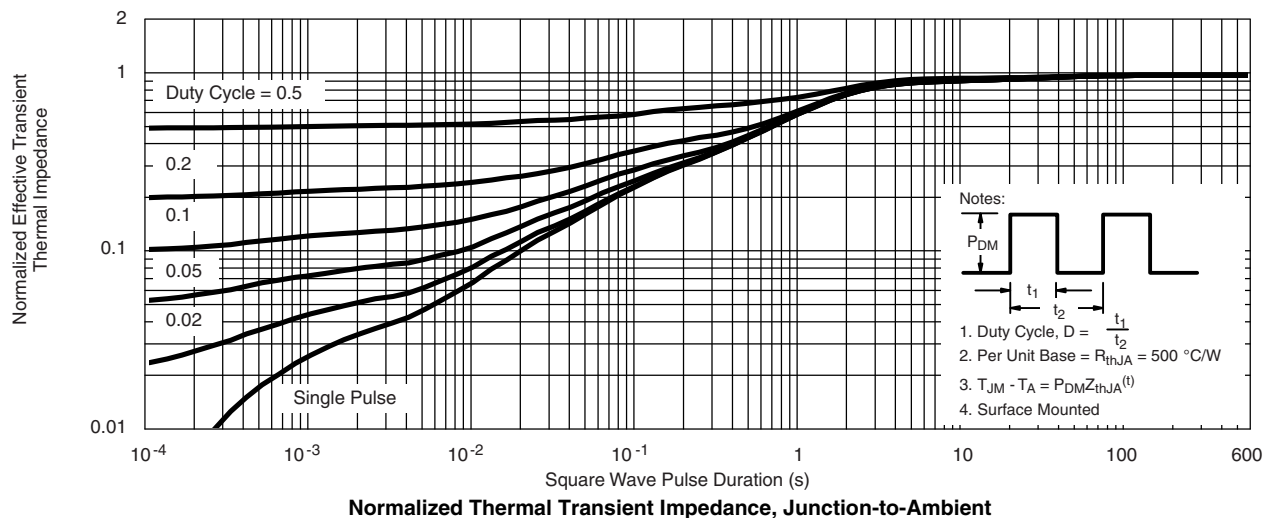
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

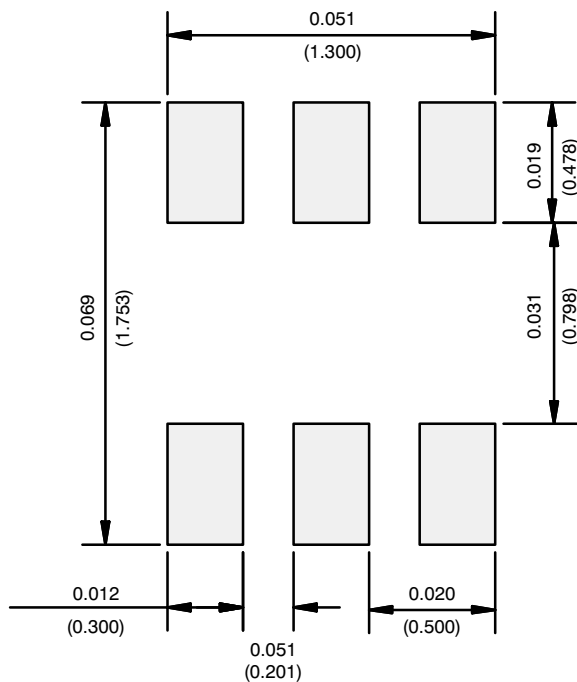


On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Threshold Voltage Variance Over Temperature


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RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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